

Product data sheet

1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in a leadless ultra small DFN1010D-3 (SOT1215) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Trench MOSFET technology
- Leadless ultra small and ultra thin SMD plastic package: 1.1 × 1.0 × 0.37 mm
- Exposed drain pad for excellent thermal conduction
- ElectroStatic Discharge (ESD) protection 1 kV HBM
- Drain-source on-state resistance R_{DSon} = 100 mΩ

3. Applications

- High-side load switch and charging switch for portable devices
- Power management in battery driven portables
- LED driver
- DC-to-DC converter

4. Quick reference data

Table 1. Qui	ck reference data						
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	-30	V
V _{GS}	gate-source voltage			-20	-	20	V
I _D	drain current	V _{GS} = -10 V; T _{amb} = 25 °C	[1]	-	-	-2.4	А
Static characte	eristics						
R _{DSon}	drain-source on-state resistance	V _{GS} = -10 V; I _D = -2.4 A; T _j = 25 °C		-	100	120	mΩ

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².





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5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		D
2	S	source		
3	D	drain	4 3	G (T
4	D	drain	Transparent top view DFN1010D-3 (SOT1215)	S 017aaa259

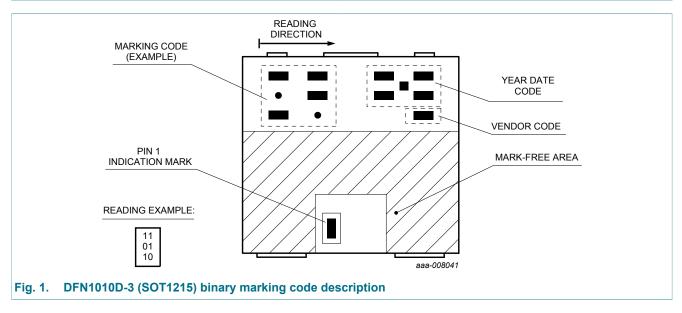
6. Ordering information

Table 3. Ordering in	formation		
Type number	Package		
	Name	Description	Version
PMXB120EPE	DFN1010D-3	plastic thermal enhanced ultra thin small outline package; no leads; 3 terminals; body 1.1 x 1.0 x 0.37 mm	SOT1215

7. Marking

Table 4. Marking codes

Type number	Marking code
PMXB120EPE	10 01 00



PMXB120EPE

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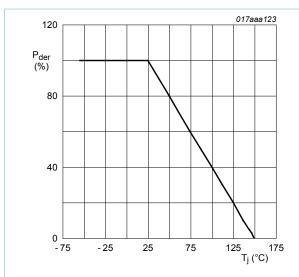
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-30	V
V _{GS}	gate-source voltage			-20	20	V
I _D	drain current	V_{GS} = -10 V; T_{amb} = 25 °C	[1]	-	-2.4	А
		V_{GS} = -10 V; T_{amb} = 100 °C	[1]	-	-1.5	А
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \ \mu s$		-	-10	А
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	0.4	W
			[1]	-	1.07	W
		T _{sp} = 25 °C		-	8.33	W
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-dra	in diode					
ls	source current	T _{amb} = 25 °C	[1]	-	-0.9	А

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.





$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

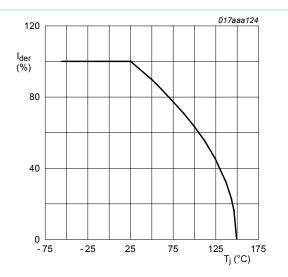
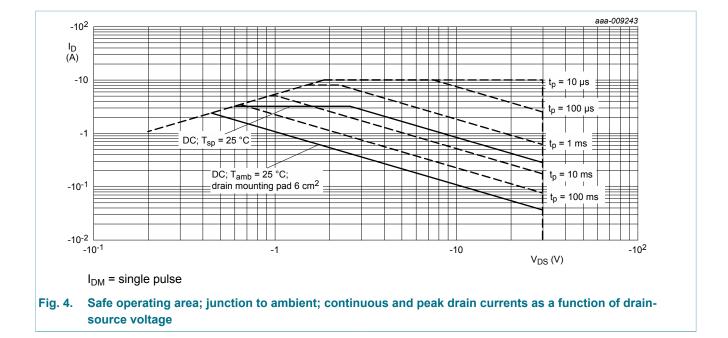


Fig. 3. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^\circ \text{C})}} \times 100 \%$$

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9. Thermal characteristics

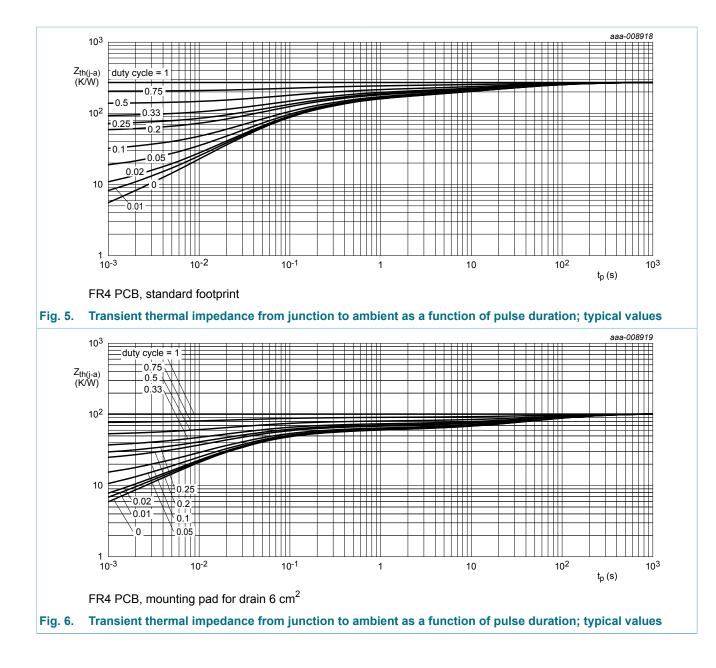
Table 6. The	rmal characteristics						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
ui()-a)	thermal resistance		[1]	-	271	312	K/W
	from junction to ambient		[2]	-	102	117	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	10	15	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².



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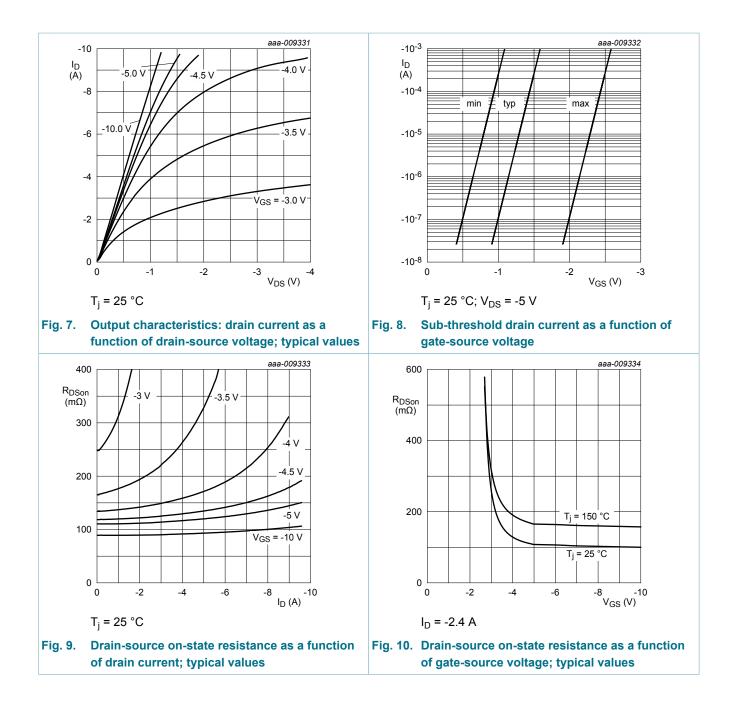
10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	octeristics					
V _{(BR)DSS}	drain-source breakdown voltage	I _D = -250 μA; V _{GS} = 0 V; T _j = 25 °C	-30	-	-	V
V _{GSth}	gate-source threshold voltage	I_D = -250 µA; V_{DS} = V_{GS} ; T_j = 25 °C	-1	-1.5	-2.5	V
I _{DSS}	drain leakage current	V_{DS} = -30 V; V_{GS} = 0 V; T_j = 25 °C	-	-	-1	μA
I _{GSS}	gate leakage current	V_{GS} = 16 V; V_{DS} = 0 V; T_j = 25 °C	-	-	10	μA
		V_{GS} = -16 V; V_{DS} = 0 V; T_j = 25 °C	-	-	-10	μA
		V _{GS} = 10 V; V _{DS} = 0 V; T _j = 25 °C	-	-	1	μA
		V_{GS} = -10 V; V_{DS} = 0 V; T_j = 25 °C	-	-	-1	μA
R _{DSon}	drain-source on-state	V_{GS} = -10 V; I _D = -2.4 A; T _j = 25 °C	-	100	120	mΩ
resis	resistance	V _{GS} = -10 V; I _D = -2.4 A; T _j = 150 °C	-	156	187	mΩ
		V_{GS} = -4.5 V; I _D = -2 A; T _j = 25 °C	-	125	170	mΩ
9 _{fs}	forward transconductance	V _{DS} = -10 V; I _D = -2.4 A; T _j = 25 °C	-	5	-	S
R _G	gate resistance	f = 1 MHz	-	14.5	-	Ω
Dynamic ch	aracteristics		I			
Q _{G(tot)}	total gate charge	V_{DS} = -15 V; I _D = -2.4 A; V _{GS} = -10 V;	-	6.2	11	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	0.9	-	nC
Q _{GD}	gate-drain charge		-	1.1	-	nC
C _{iss}	input capacitance	V _{DS} = -15 V; f = 1 MHz; V _{GS} = 0 V;	-	309	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	41	-	pF
C _{rss}	reverse transfer capacitance		-	32	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = -15 V; I _D = -2.4 A; V _{GS} = -10 V;	-	4	-	ns
t _r	rise time	R _{G(ext)} = 6 Ω; T _j = 25 °C	-	11	-	ns
t _{d(off)}	turn-off delay time		-	16	-	ns
t _f	fall time		-	7	-	ns
Source-drai	n diode		1	1		
V _{SD}	source-drain voltage	I _S = -0.9 A; V _{GS} = 0 V; T _j = 25 °C	-	-0.8	-1.2	V

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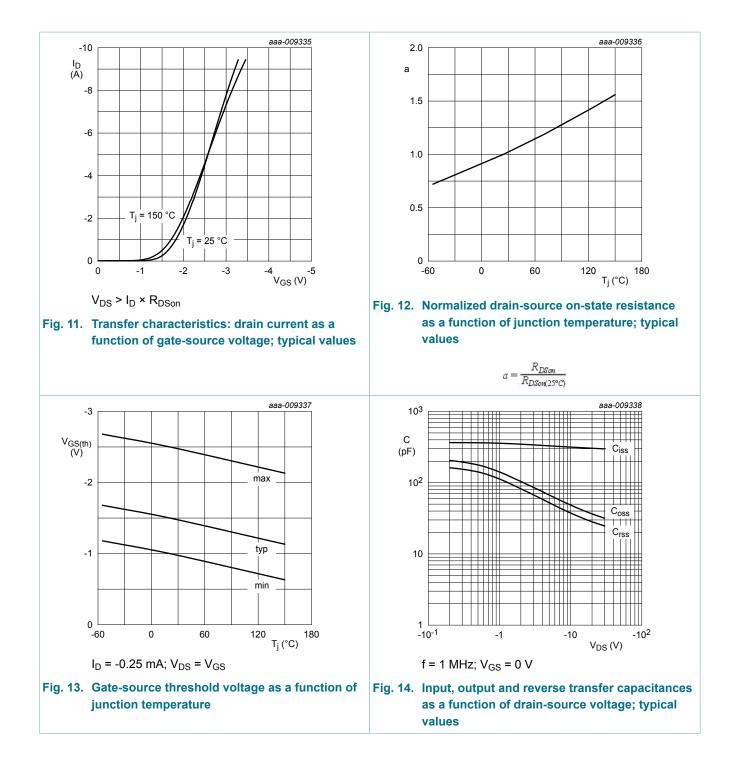
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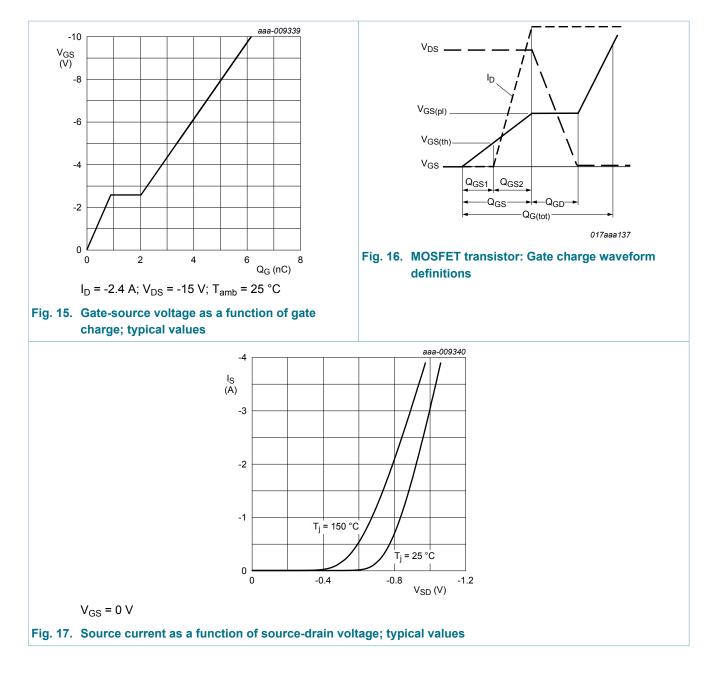
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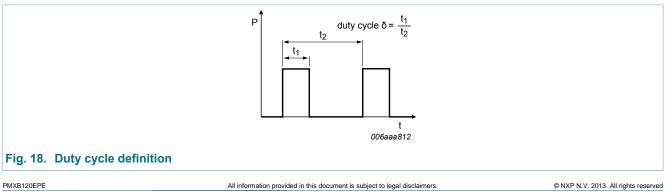
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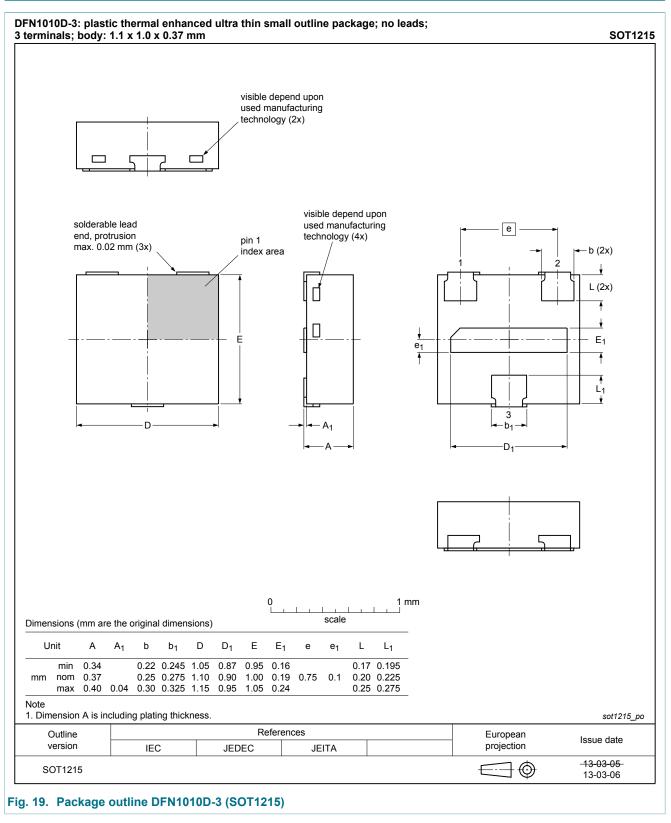


11. Test information



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12. Package outline



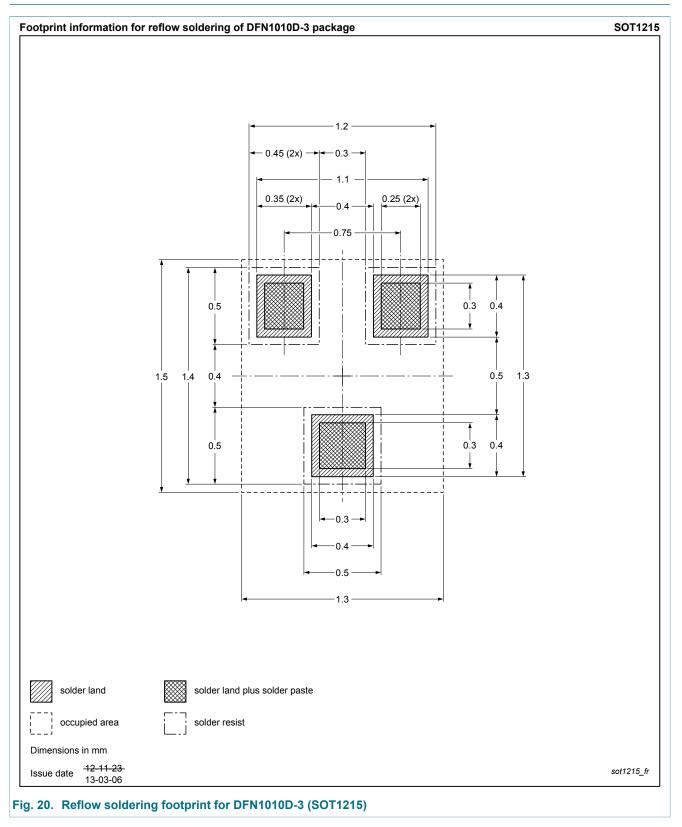
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13. Soldering



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14. Revision history

Table 8. Revision his	story			
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMXB120EPE v.1	20130924	Product data sheet	-	-

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15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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